UNISONIC TECHNOLOGIES CO., LTD

4NM70A Power MOSFET

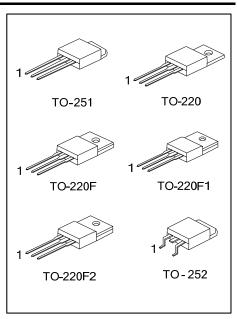
4A, 700V N-CHANNEL SUPER-JUNCTION MOSFET

DESCRIPTION

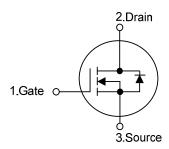
The UTC 4NM70A is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

- * $R_{DS(ON)}$ < 1.8 Ω @ V_{GS} = 10 V, I_D = 2.0 A
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, High Ruggedness



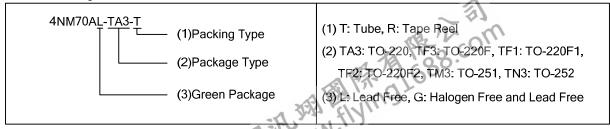
SYMBOL



ORDERING INFORMATION

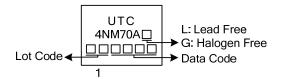
Ordering Number		Dookogo	Pin Assignment			Deaking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
4NM70AL-TA3-T	4NM70AG-TA3-T	TO-220	G	D	S	Tube	
4NM70AL-TF3-T	4NM70AG-TF3-T	TO-220F	G	D	S	Tube	
4NM70AL-TF1-T	4NM70AG-TF1-T	TO-220F1	G	D	S	Tube	
4NM70AL-TF2-T	4NM70AG-TF2-T	TO-220F2	G	D	S	Tube	
4NM70AL-TM3-T	4NM70AG-TM3-T	TO-251	G	D	S	Tube	
4NM70AL-TN3-R	4NM70AG-TN3-R	TO-252	G	D	S	Tape Reel	

Note: Pin Assignment: G: Gate D: Drain S: Source



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MARKING





ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	±30	V
Drain Current	Continuous	I_{D}	4	Α
	Pulsed (Note 2)	I_{DM}	16	Α
Avalanche Current (Note 2)		I _{AR}	1.14	Α
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	90	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.7	V/ns
Power Dissipation	TO-220		106	W
	TO-220F/TO-220F1 TO-220F2	P_D	36	W
	TO-251/TO-252		49	W
Junction Temperature		TJ	+150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

- 2. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 3. L = 138mH, I_{AS} = 1.14A, V_{DD} = 50V, R_{G} = 25 Ω , Starting T_{J} = 25°C
- 4. $I_{SD} \le 4.0A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$

THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2	θ_{JA}	62.5	°C/W	
	TO-251/TO-252		110	°C/W	
Junction to Case	TO-220		1.18	°C/W	
	TO-220F/TO-220F1 TO-220F2	θ_{JC}	3.47	°C/W	
	TO-251/TO-252		2.55	°C/W	



ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise specified)

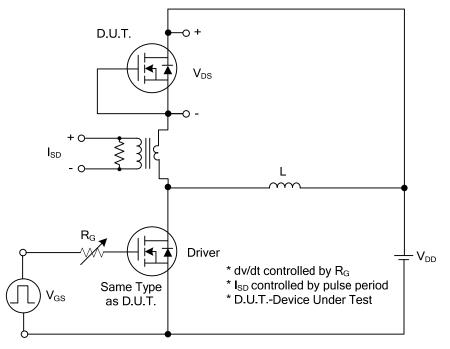
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS			•		•			
Drain-Source Breakdown Voltage		BV _{DSS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	700			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 700 V, V _{GS} = 0 V			10	μA	
Gate-Source Leakage Current	Forward		$V_{GS} = 30 \text{ V}, V_{DS} = 0 \text{ V}$			100	π Λ	
	Reverse	I _{GSS}	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA	
ON CHARACTERISTICS								
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$			4.5	V	
Static Drain-Source On-State Resistance		R _{DS(ON)}	$V_{GS} = 10 \text{ V}, I_D = 2.0 \text{ A}$			1.8	Ω	
DYNAMIC CHARACTERISTICS								
Input Capacitance	nput Capacitance				275		pF	
Output Capacitance		Coss	V_{GS} =0V, V_{DS} =25V, f =1MHz		130		pF	
Reverse Transfer Capacitance		C_{RSS}			17		pF	
SWITCHING CHARACTERISTIC	S				-	=	-	
Total Gate Charge (Note 1)		Q_G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A,		35		nC	
Gate to Source Charge		Q_GS	$V_{DS}=50V$, $V_{GS}=10V$, $I_{D}=1.3A$, $-I_{D}=100\mu A$ (Note 1, 2)		4		nC	
Gate to Drain Charge		Q_GD	1D=100μA (Note 1, 2)		7.5		nC	
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$			40		ns	
Rise Time		t_R	V_{DS} =30V, V_{GS} =10V, I_{D} =0.5A,		54		ns	
Turn-OFF Delay Time		$t_{D(OFF)}$	R_G =25 Ω (Note 1, 2)		110		ns	
Fall-Time		t_{F}			23		ns	
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS								
Maximum Body-Diode Continuous Current		Is				4	Α	
Maximum Body-Diode Pulsed Current		I _{SM}				16	Α	
Drain-Source Diode Forward Voltage (Note 1)		V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 4.0 \text{ A}$			1.4	V	
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	$V_{GS} = 0 \text{ V}, I_S = 4.0 \text{ A},$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$		290		ns	
Body Diode Reverse Recovery Charge		Q_{rr}			2		μC	

Notes: 1. Pulse Test: Pulse width ≤ 300µs, Duty cycle ≤ 2%.

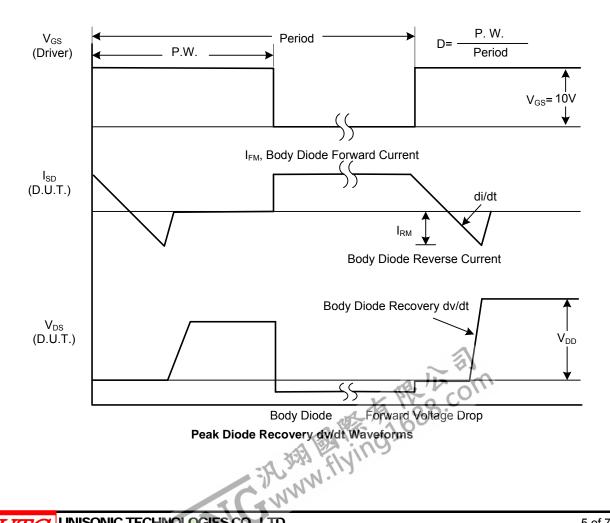


^{2.} Essentially independent of operating temperature.

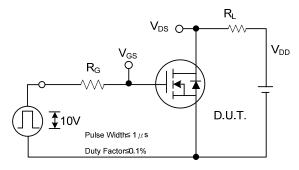
TEST CIRCUITS AND WAVEFORMS



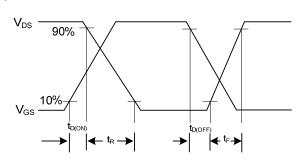
Peak Diode Recovery dv/dt Test Circuit



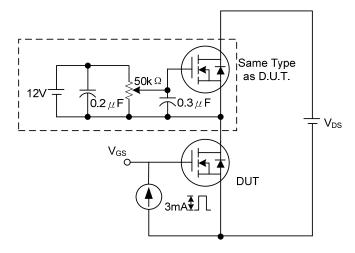
TEST CIRCUITS AND WAVEFORMS (Cont.)



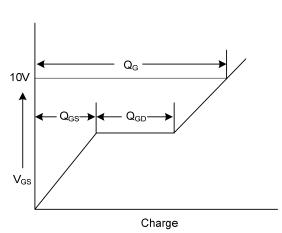
Switching Test Circuit



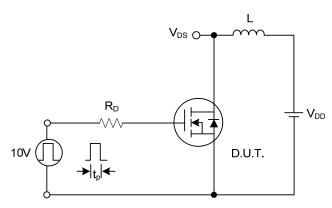
Switching Waveforms



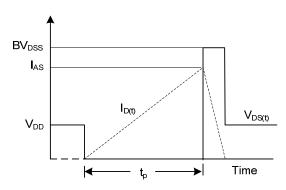
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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